

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace, without prejudice, all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1-10 (canceled).

11. (Currently Amended) An electric semiconductor component, comprising:
a monocrystalline semiconductor substrate;
an insulation layer arranged on a surface of the semiconductor substrate and penetrated by at least one contact hole in at least one location; and

a contact structure that contacts the semiconductor substrate through the contact hole and made of a material in which a semiconductor material of the semiconductor substrate is soluble in an anisotropic dissolving process;

wherein edges of the contact hole include diffusion stop structures, and wherein the diffusion stop structures include curved segments.

12. (Canceled).

13. (Currently Amended) The semiconductor component according to claim [[12]] 11, wherein the contact hole is shaped one of circular and as overlapping intersecting circles.

14. (Currently Amended) ~~The semiconductor component according to claim 11,~~ An electric semiconductor component, comprising:

a monocrystalline semiconductor substrate;
an insulation layer arranged on a surface of the semiconductor substrate and penetrated by at least one contact hole in at least one location; and

a contact structure that contacts the semiconductor substrate through the contact hole and made of a material in which a semiconductor material of the semiconductor substrate is soluble in an anisotropic dissolving process;

wherein edges of the contact hole include diffusion stop structures,
and wherein the diffusion stop structures include microstructured sections of the edges.

15. (Previously Presented) The semiconductor component according to claim 14, wherein the microstructured sections include one of a crenellated and a sawtooth pattern.

16. (Previously Presented) The semiconductor component according to claim 15, wherein the one of the crenellated and the sawtooth pattern includes a plurality of projections, each projection having an edge length of at most 2 μm .

17. (Previously Presented) The semiconductor component according to claim 11, wherein the semiconductor material includes at least one class of crystal planes that is subject to one of little and no attack in the dissolving process, and the diffusion stop structures include rectilinear sections of the edges intersecting the crystal planes of the class of crystal planes extending in the semiconductor substrate beneath the contact hole.

18. (Currently Amended) ~~The semiconductor component according to claim 11;~~ An electric semiconductor component, comprising:

a monocrystalline semiconductor substrate;
an insulation layer arranged on a surface of the semiconductor substrate and penetrated by at least one contact hole in at least one location; and

a contact structure that contacts the semiconductor substrate through the contact hole and made of a material in which a semiconductor

material of the semiconductor substrate is soluble in an anisotropic dissolving process;

wherein edges of the contact hole include diffusion stop structures,
and wherein the contact hole is shaped as one of an equilateral triangle and overlapping, intersecting equilateral triangles.

19. (Previously Presented) The semiconductor component according to claim 11, wherein the semiconductor substrate includes a $\langle 111 \rangle$ Si substrate.

20. (Previously Presented) The semiconductor component according to claim 19, wherein the edges of the contact hole are rotated by approximately $\pm 15^\circ$ toward lines of intersection of one of the $\langle 11\bar{1} \rangle$, $\langle 1\bar{1}1 \rangle$ and $\langle \bar{1}11 \rangle$ crystal planes with the surface.